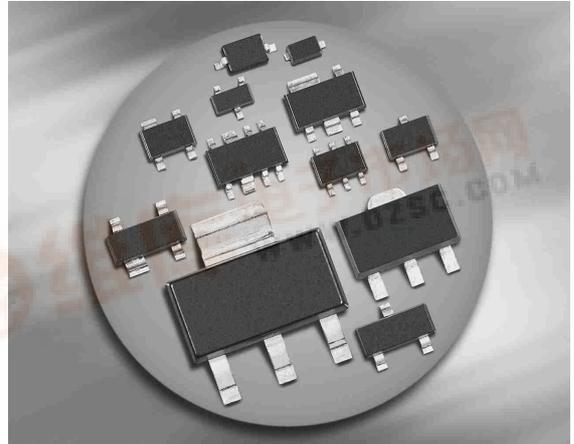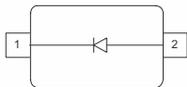**Infineon** technologies

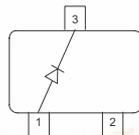# BAS40.../BAS140W

Silicon Schottky Diode

- General-purpose diode for high-speed switching
- Circuit protection
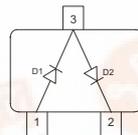- Voltage clamping
- High-level detecting and mixing
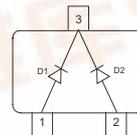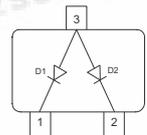

| BAS140W | BAS40 | BAS40-04 | BAS40-05 | BAS40-06 |
| BAS40-02L | | | BAS40-05W | BAS40-06W |

BAS40-07
BAS40-07W
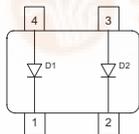
ESD: **E**lectro**s**tatic **d**ischarge sensitive device, observe handling precaution!

Type	Package	Configuration	L_S(nH)	Marking
BAS140W	SOD323	single	1.8	white 4
BAS40	SOT23	single	1.8	43s
BAS40-02L*	TSLP-2-1	single, leadless	0.4	FF
BAS40-04	SOT23	series	1.8	44s
BAS40-05	SOT23	common cathode	1.8	45s
BAS40-05W	SOT323	common cathode	1.4	45s
BAS40-06	SOT23	common anode	1.8	46s
BAS40-06W	SOT323	common anode	1.4	46s
BAS40-07	SOT143	parallel pair	2	47s
BAS40-07W	SOT343	parallel pair	1.8	47s

*Preliminary

Maximum Ratings at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	40	V
Forward current	I_F	120	mA
Non-repetitive peak surge forward current $t \leq 10ms$	I_{FSM}	200	
Total power dissipation	P_{tot}		mW
BAS140W, $T_S \leq 113°C$		250	
BAS40, BAS40-07, $T_S \leq 81°C$		250	
BAS40-02L, $T_S \leq 127°C$		250	
BAS40-04, BAS40-06, $T_S \leq 56°C$		250	
BAS40-06W, $T_S \leq 106°C$		250	
BAS40-05, $T_S \leq 31°C$		250	
BAS40-05W, $T_S \leq 98°C$		250	
BAS40-07W, $T_S \leq 118°C$		250	
Junction temperature	T_j	150	°C
Operating temperature range	T_{op}	-55 ... 125	
Storage temperature	T_{stg}	-55 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point[1]	R_{thJS}		K/W
BAS140W		≤ 150	
BAS40, BAS40-07		≤ 275	
BAS40-02L		≤ 90	
BAS40-04, BAS40-06		≤ 375	
BAS40-06W		≤ 175	
BAS40-05		≤ 475	
BAS40-05W		≤ 205	
BAS40-07W		≤ 125	

[1]For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Breakdown voltage $I_{(BR)}$ = 10 µA	$V_{(BR)}$	40	-	-	V
Reverse current V_R = 30 V	I_R	-	-	1	µA
Forward voltage	V_F				mV
I_F = 1 mA		250	310	380	
I_F = 10 mA		350	450	500	
I_F = 40 mA		600	720	1000	
Forward voltage matching[1] I_F = 10 mA	ΔV_F	-	-	20	
AC Characteristics					
Diode capacitance V_R = 0 , f = 1 MHz	C_T	-	3	5	pF
Differential forward resistance I_F = 10 mA, f = 10 kHz	R_F	-	10	-	Ω
Charge carrier life time I_F = 25 mA	τ_{rr}	-	-	100	ps

[1]ΔV_F is the difference between lowest and highest V_F in a multiple diode component.

Diode capacitance $C_T = f\ (V_R)$

f = 1MHz

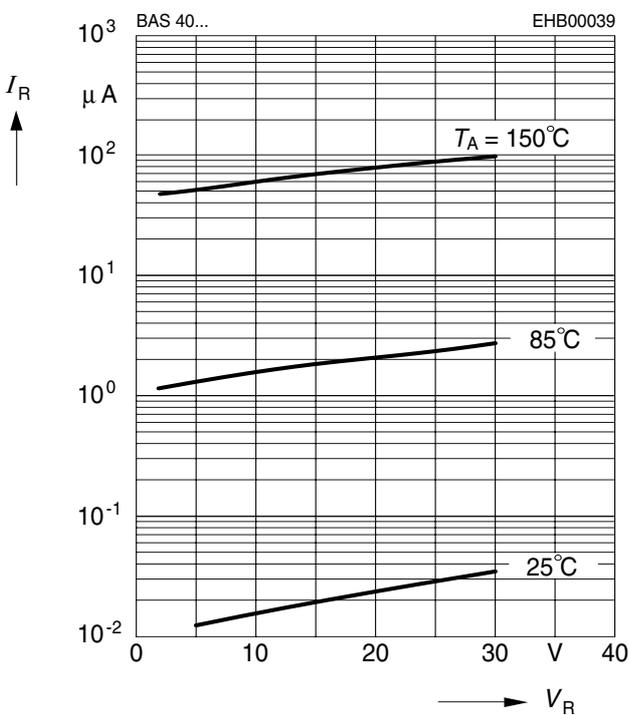BAS 40...   EHB00040
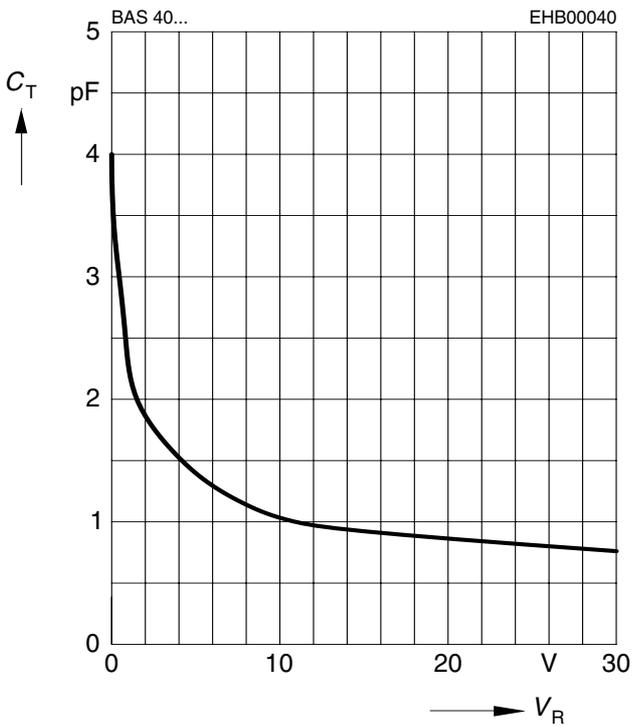
Forward resistance $r_f = f\ (I_F)$

f = 10 kHz

BAS 40...   EHB00041
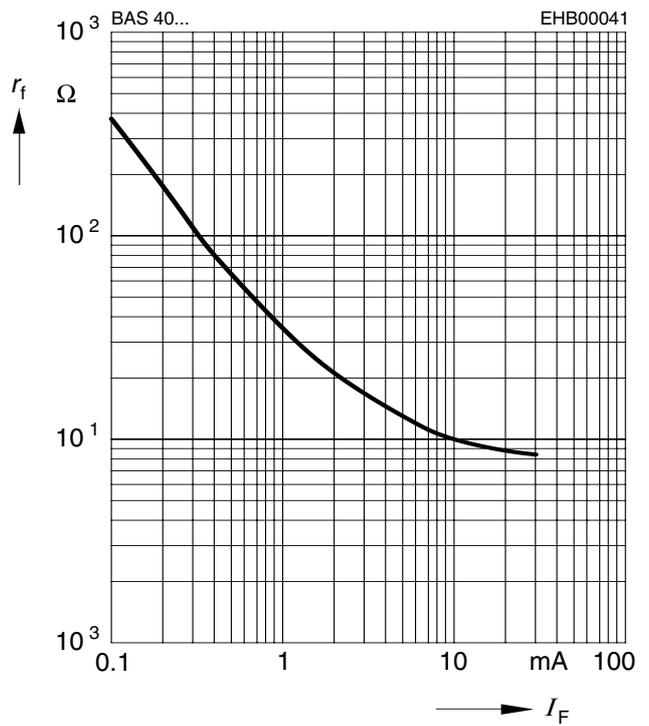
Reverse current $I_R = f(V_R)$

T_A = Parameter

BAS 40...   EHB00039

T_A = 150°C

85°C

25°C

Forward current $I_F = f\ (V_F)$

T_A = Parameter

BAS 40...   EHB00038

T_A = -40 °C
25 °C
85 °C
150 °C
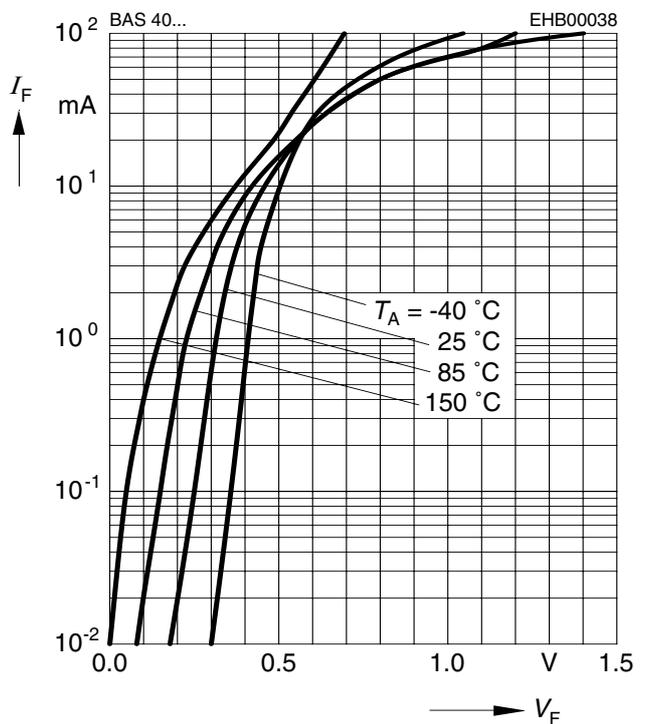
Forward current $I_F = f(T_S)$

BAS140W
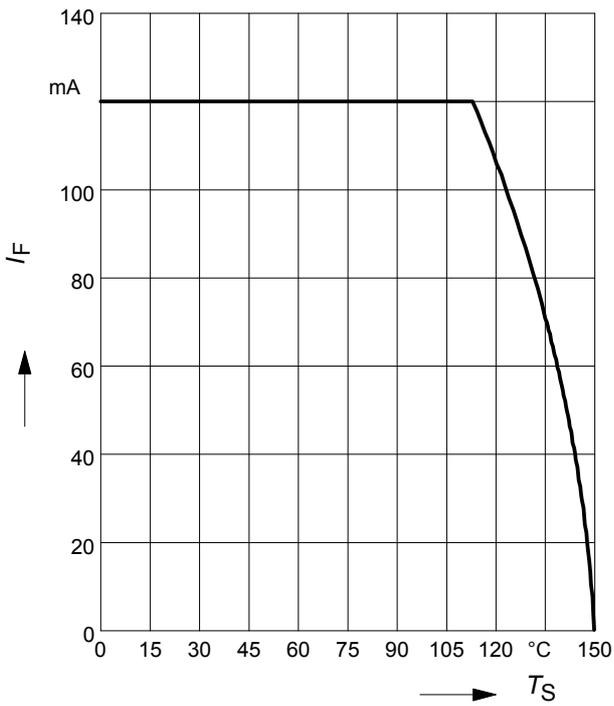
Forward current $I_F = f(T_S)$

BAS40, BAS40-07
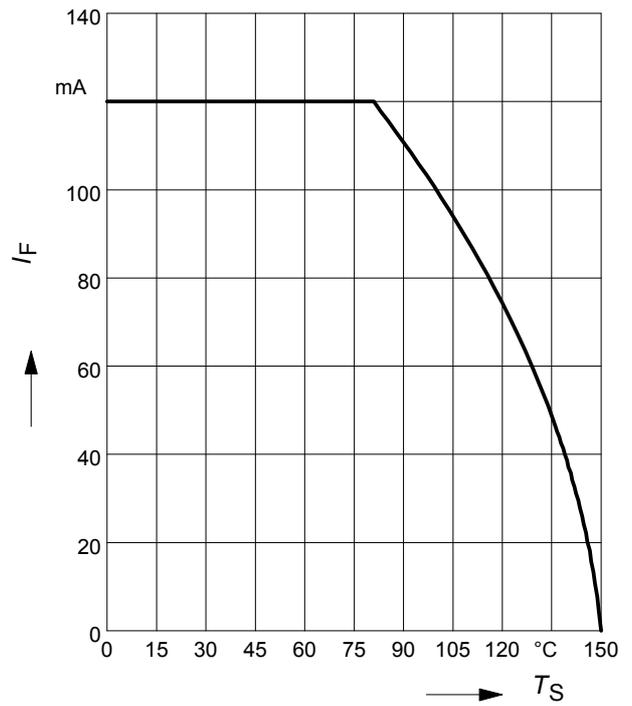
Forward current $I_F = f(T_S)$

BAS40-02L
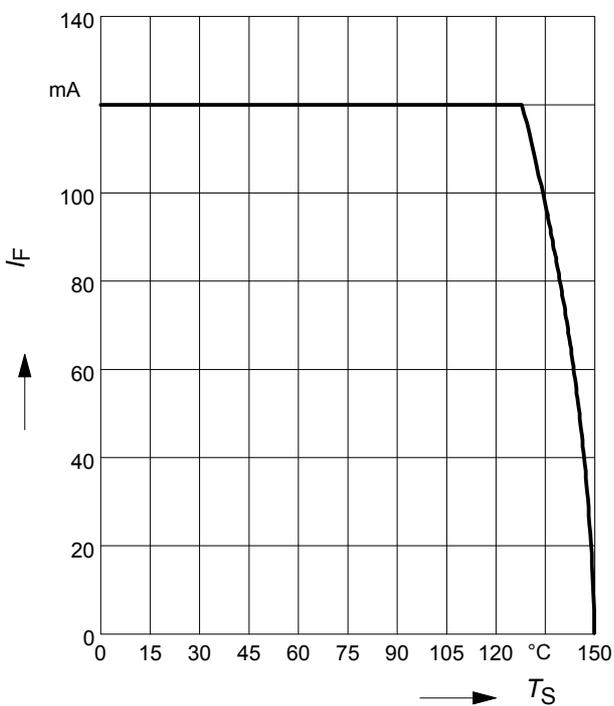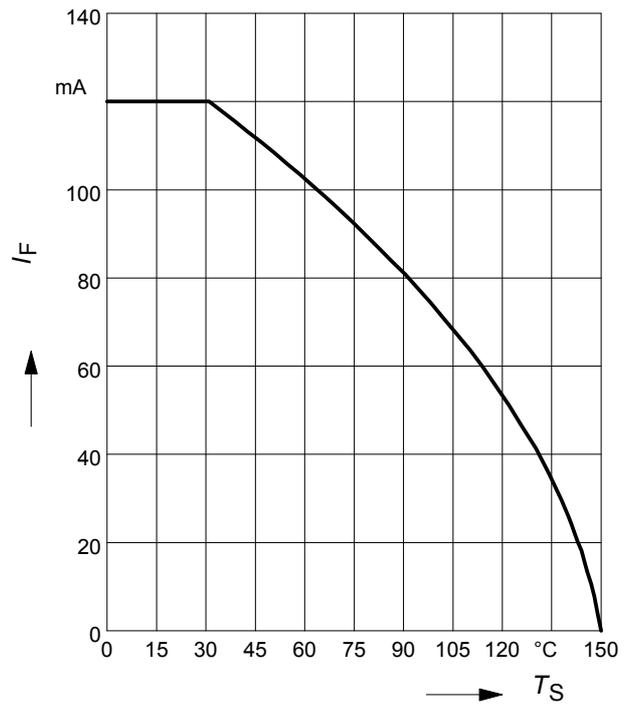

Forward current $I_F = f(T_S)$

BAS40-04, BAS40-06
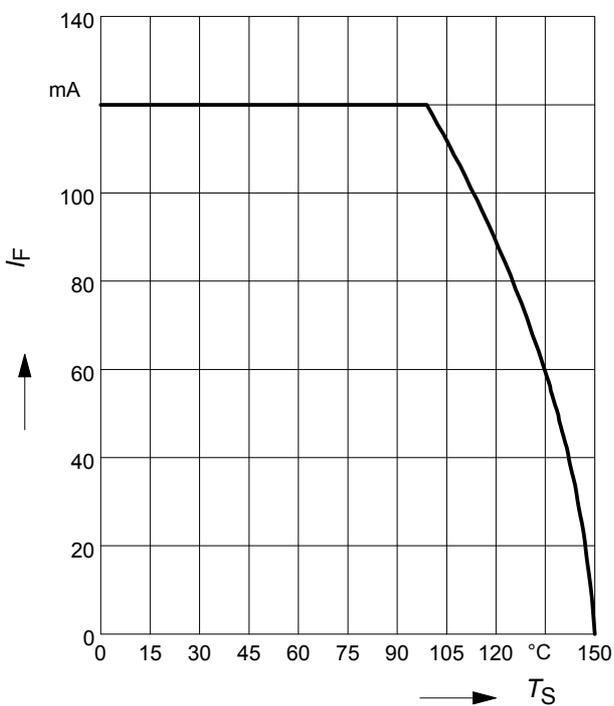
Jan-16-2004
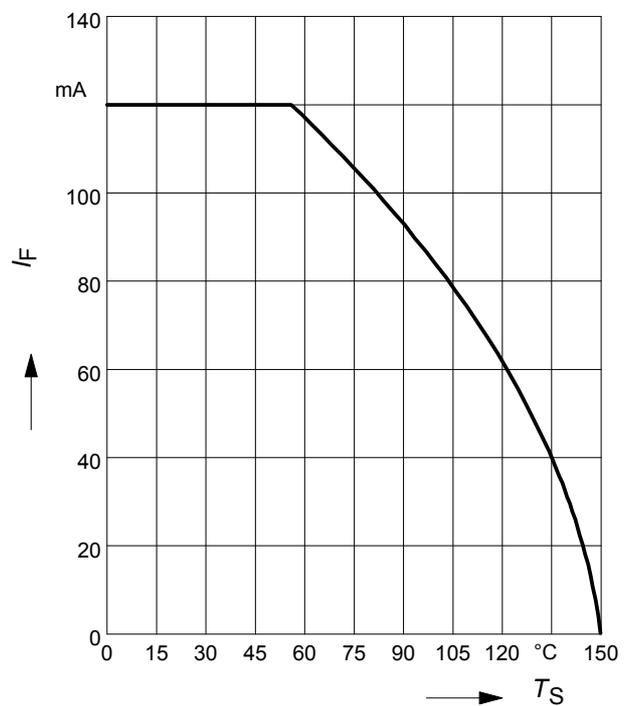
Forward current $I_F = f(T_S)$

BAS40-06W
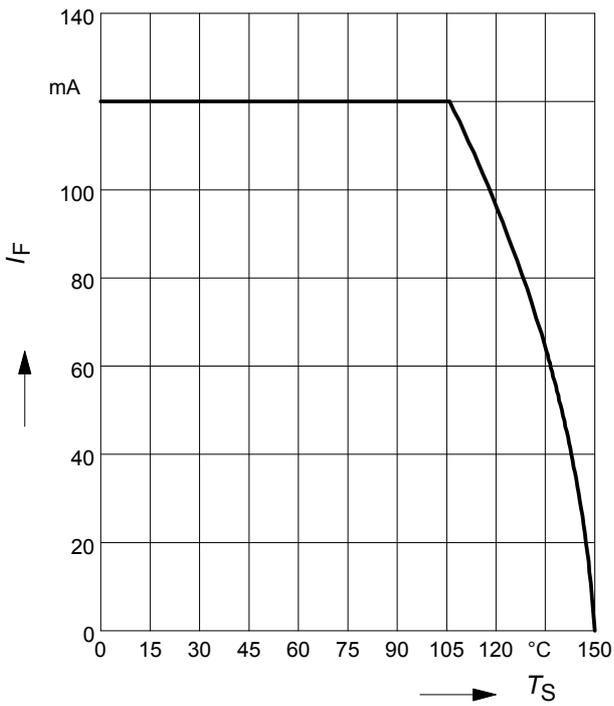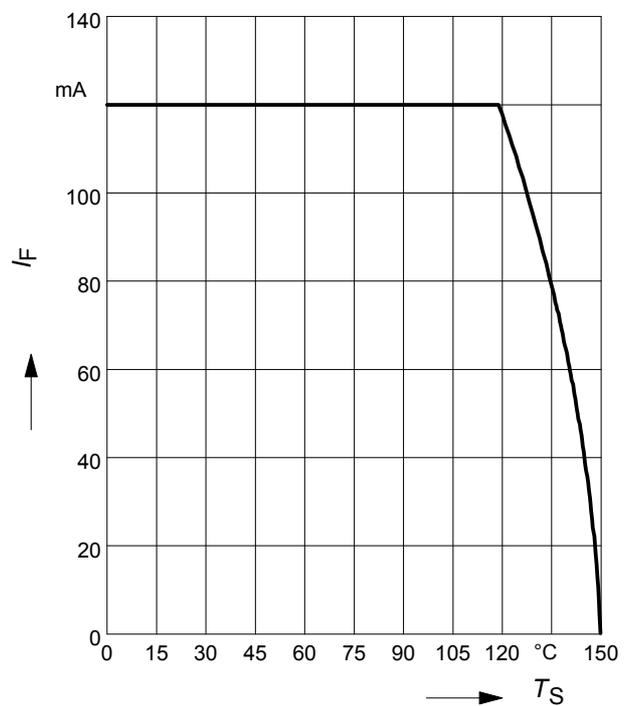

Forward current $I_F = f(T_S)$

BAS40-05

Forward current $I_F = f(T_S)$

BAS40-05W

Forward current $I_F = f(T_S)$

BAS40-07W

Jan-16-2004

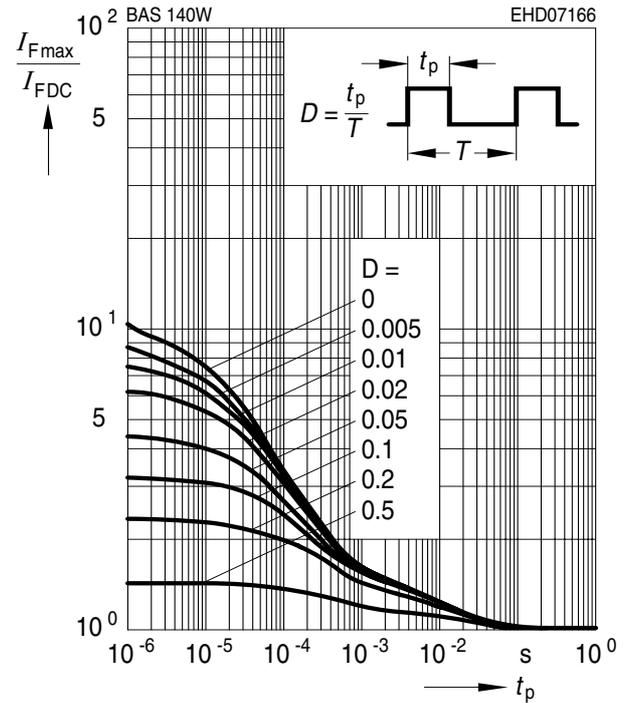## Permissible Puls Load $R_{thJS} = f(t_p)$
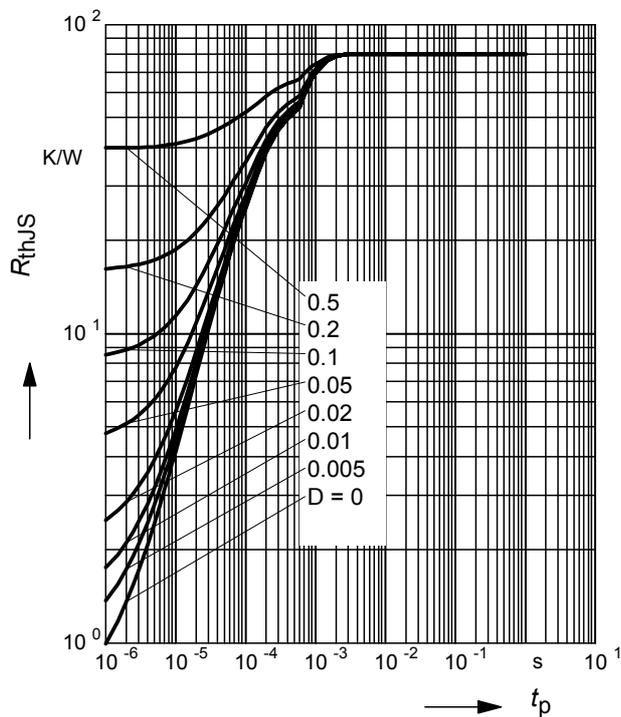BAS140W
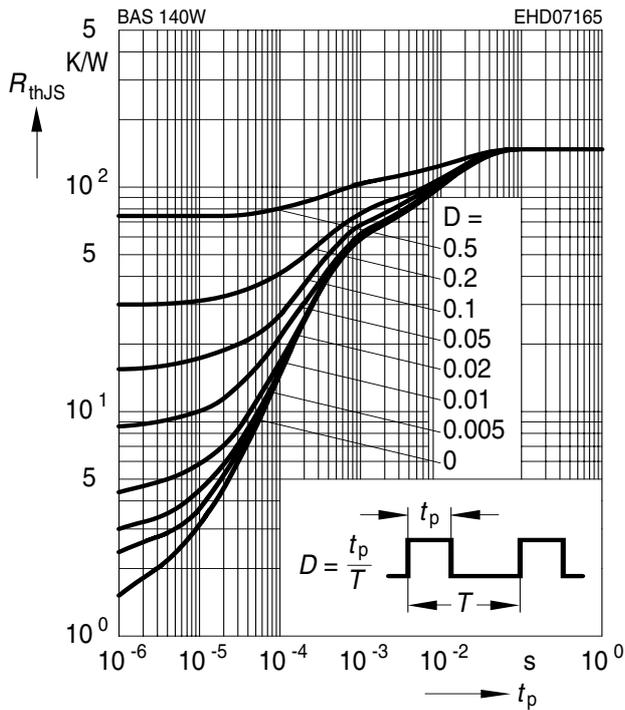
Permissible Pulse Load
$I_{Fmax}/I_{FDC} = f(t_p)$
BAS140W
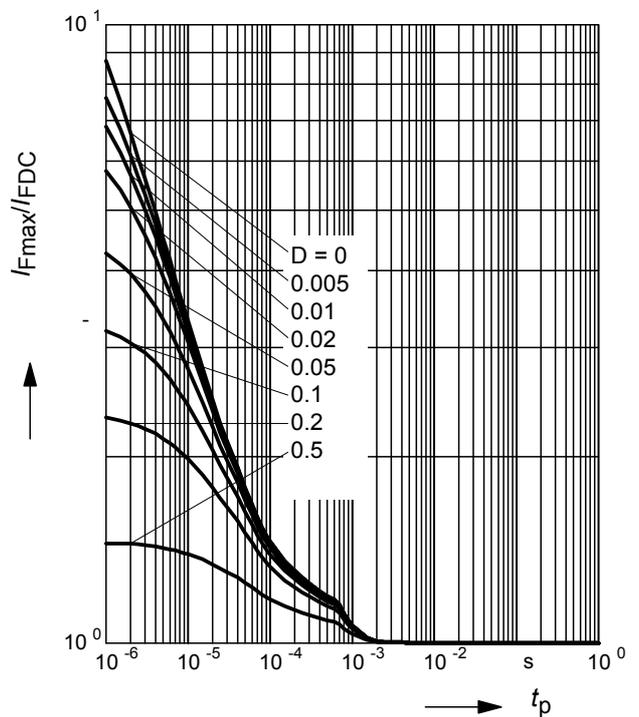

Permissible Puls Load $R_{thJS} = f(t_p)$
BAS40-02L
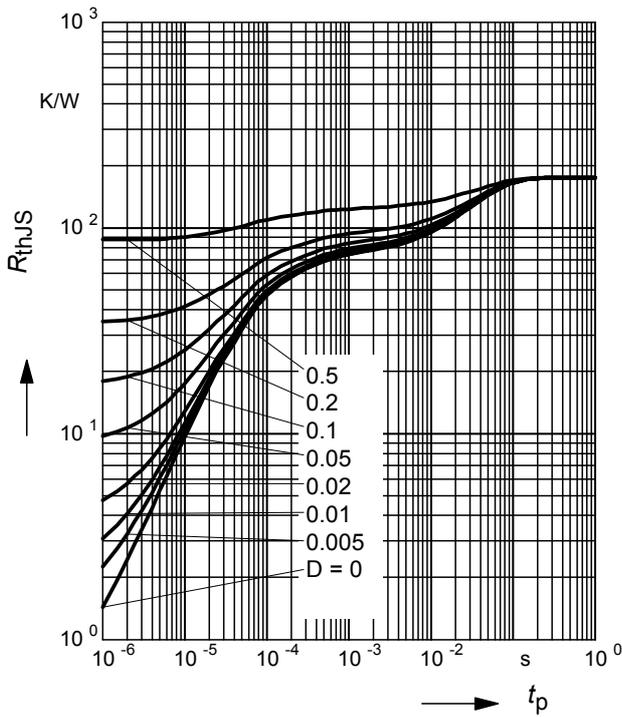

Permissible Pulse Load
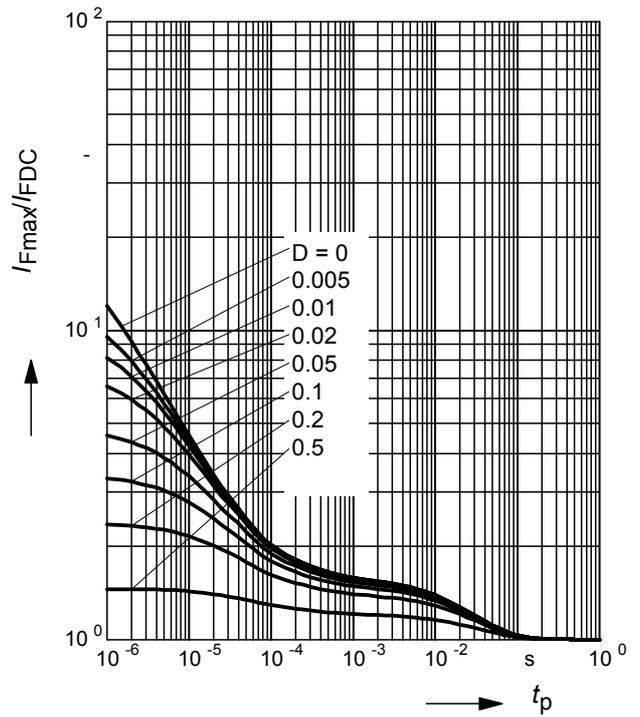$I_{Fmax}/I_{FDC} = f(t_p)$ BAS40-02L

7

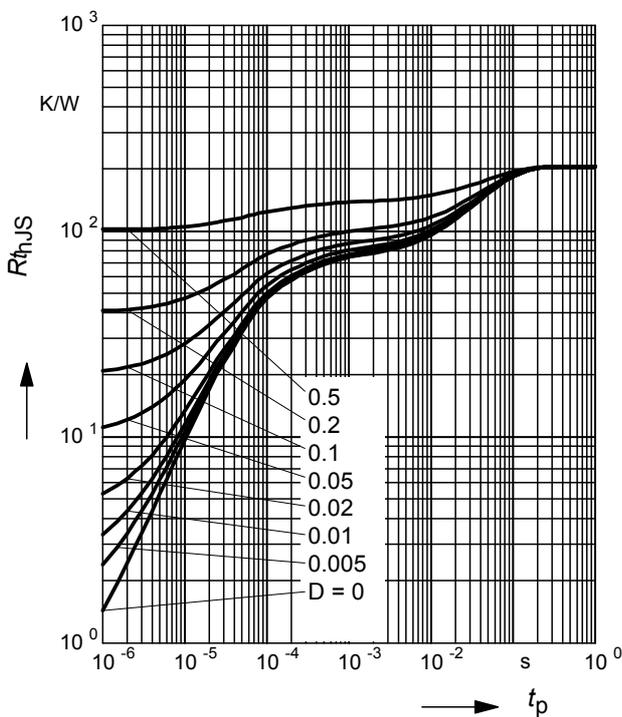**Permissible Puls Load** $R_{thJS} = f(t_p)$

BAS40-06W

Permissible Pulse Load

$I_{Fmax}/I_{FDC} = f(t_p)$ BAS40-06W

Permissible Puls Load $R_{thJS} = f(t_p)$

BAS40-05W

Permissible Pulse Load

$I_{Fmax}/I_{FDC} = f(t_p)$ BAS40-05W